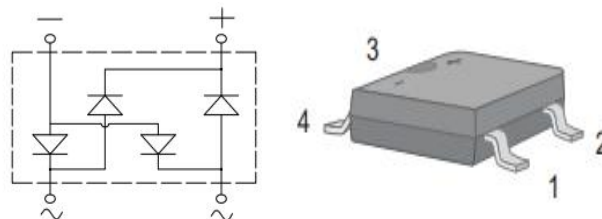


Bridge Rectifier Diode 整流桥

■ Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Reflow Solder Temperature 220°C 回流焊温度 220 度
Package 封装: MBF



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	UMB 05F	UMB 1F	UMB 2F	UMB 4F	UMB 6F	UMB 8F	UMB 10F	Unit 单位
Marking 印字		MB05F	MB1F	MB2F	MB4F	MB6F	MB8F	MB10F	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	1							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	75							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	V_F		1		V	$I_F=0.5\text{A}$
Reverse Current ($T_A=25^{\circ}\text{C}$) 反向漏电流($T_A=125^{\circ}\text{C}$)	I_R			5 500	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		18		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

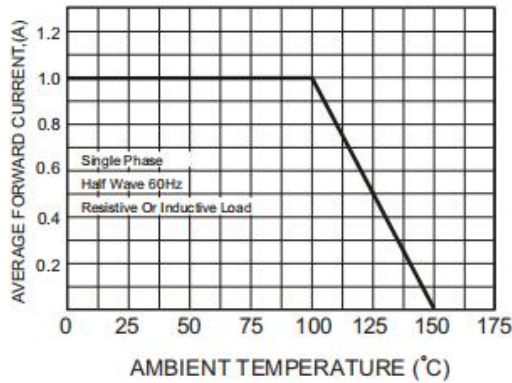


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

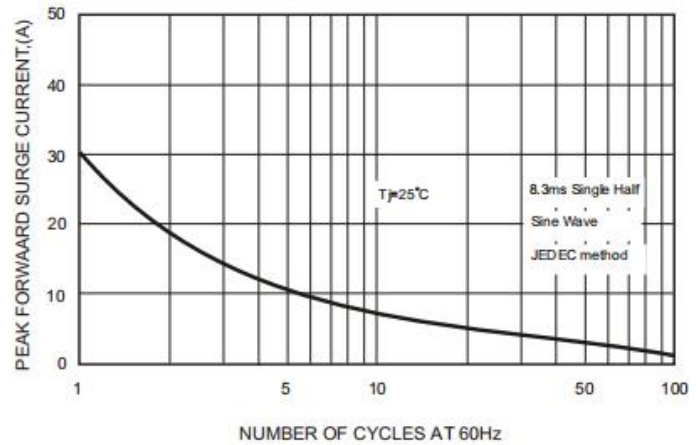


FIG.3-TYPICAL FORWARD CHARACTERISTICS

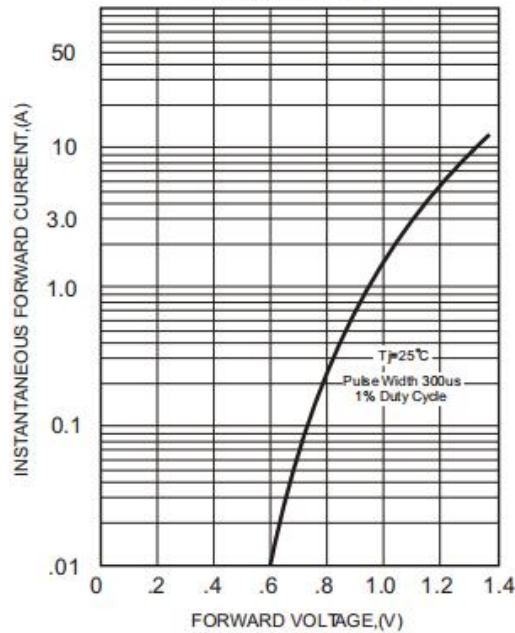
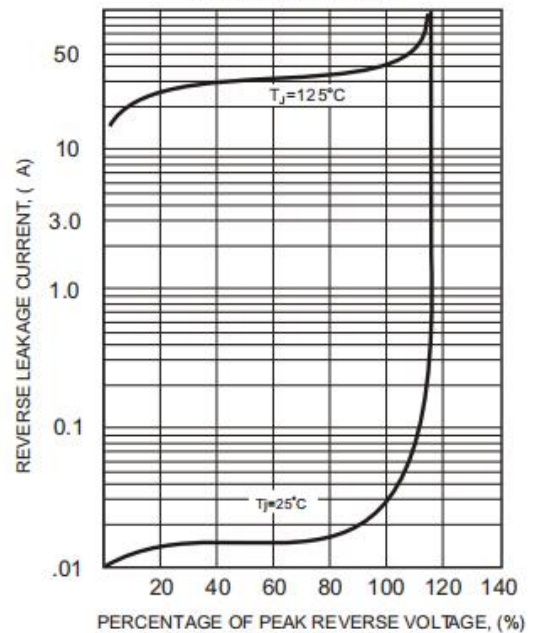
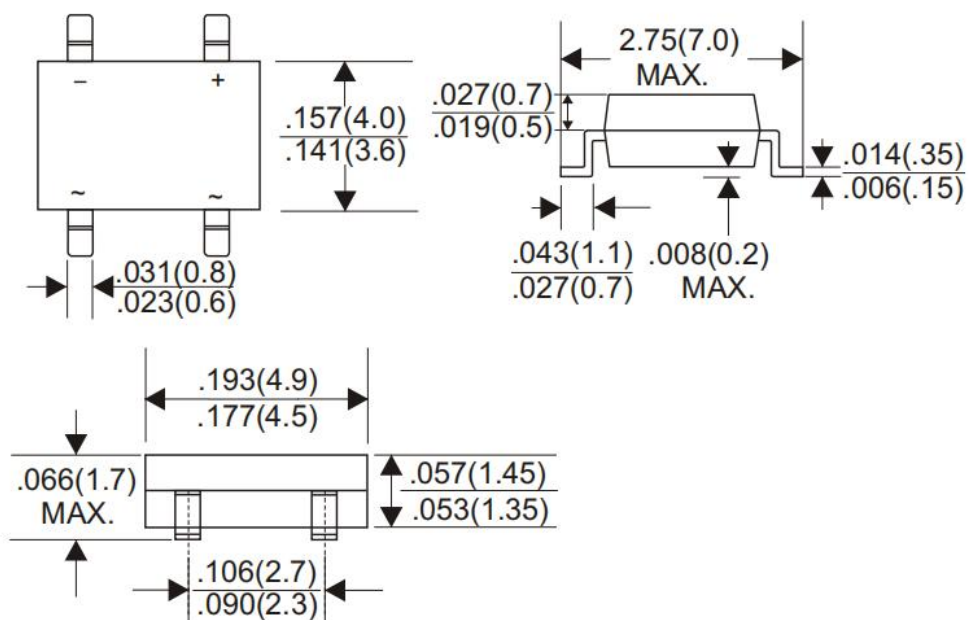


FIG.4-TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸

MBF



Dimensions in inches and (millimeters)